

Silicon PNP Power Transistors

2SB1605 2SB1605A

**DESCRIPTION**

- With TO-220F package
- Low collector saturation voltage
- Good linearity of  $h_{FE}$

**APPLICATIONS**

- For low-voltage switching applications

**PINNING**

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

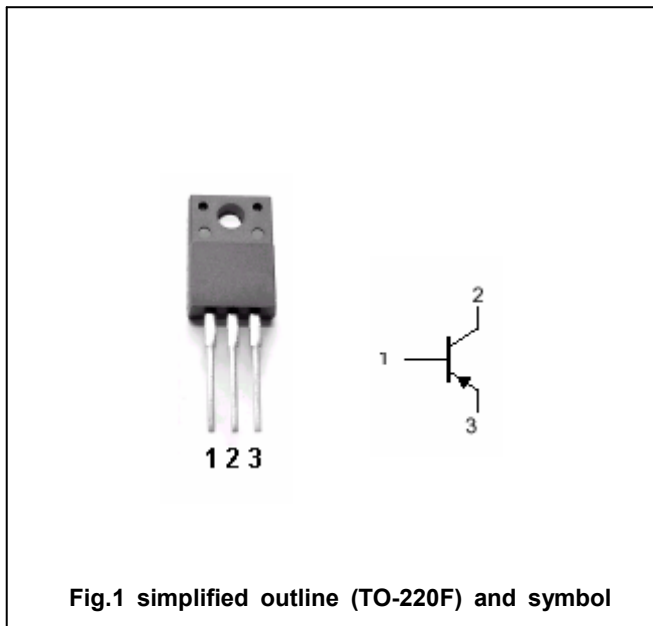


Fig.1 simplified outline (TO-220F) and symbol

**Absolute maximum ratings (Ta=25°C)**

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
V <sub>CBO</sub>	Collector-base voltage	2SB1605	-60	V
		2SB1605A	-80	
V <sub>CEO</sub>	Collector-emitter voltage	2SB1605	-60	V
		2SB1605A	-80	
V <sub>EBO</sub>	Emitter-base voltage	Open collector	-5	V
I <sub>C</sub>	Collector current		-3	A
I <sub>CM</sub>	Collector current-peak		-5	A
P <sub>C</sub>	Collector dissipation	T <sub>a</sub> =25°C	2	W
		T <sub>C</sub> =25°C	35	
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-55~150	°C

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	2SB1605	I <sub>C</sub> =-30mA ; I <sub>B</sub> =0	-60			V
		2SB1605A		-80			
V <sub>CEsat</sub>	Collector-emitter saturation voltage		I <sub>C</sub> =-3A ; I <sub>B</sub> =-0.375A			-1.2	V
V <sub>BE</sub>	Base-emitter on voltage		I <sub>C</sub> =-3A ; V <sub>CE</sub> =-4V			-1.8	V
I <sub>CES</sub>	Collector cut-off current	2SB1605	V <sub>CE</sub> =-60V ; V <sub>BE</sub> =0			-200	μA
		2SB1605A	V <sub>CE</sub> =-80V ; V <sub>BE</sub> =0				
I <sub>CEO</sub>	Collector cut-off current	2SB1605	V <sub>CE</sub> =-30V ; I <sub>B</sub> =0			-300	μA
		2SB1605A	V <sub>CE</sub> =-60V ; I <sub>B</sub> =0				
I <sub>EBO</sub>	Emitter cut-off current		V <sub>EB</sub> =-5V ; I <sub>C</sub> =0			-1	mA
h <sub>FE-1</sub>	DC current gain		I <sub>C</sub> =-1A ; V <sub>CE</sub> =-4V	70		250	
h <sub>FE-2</sub>	DC current gain		I <sub>C</sub> =-3A ; V <sub>CE</sub> =-4V	10			
f <sub>T</sub>	Transition frequency		I <sub>C</sub> =-0.5A ; V <sub>CE</sub> =-10V		30		MHz

## Switching times

t <sub>on</sub>	Turn-on time	I <sub>C</sub> =-1A ; I <sub>B1</sub> =-I <sub>B2</sub> =-0.1A		0.5		μs
t <sub>stg</sub>	Storage time			1.2		μs
t <sub>f</sub>	Fall time			0.3		μs

◆ h<sub>FE-1</sub> Classifications

Q	P
70-150	120-250

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PACKAGE OUTLINE

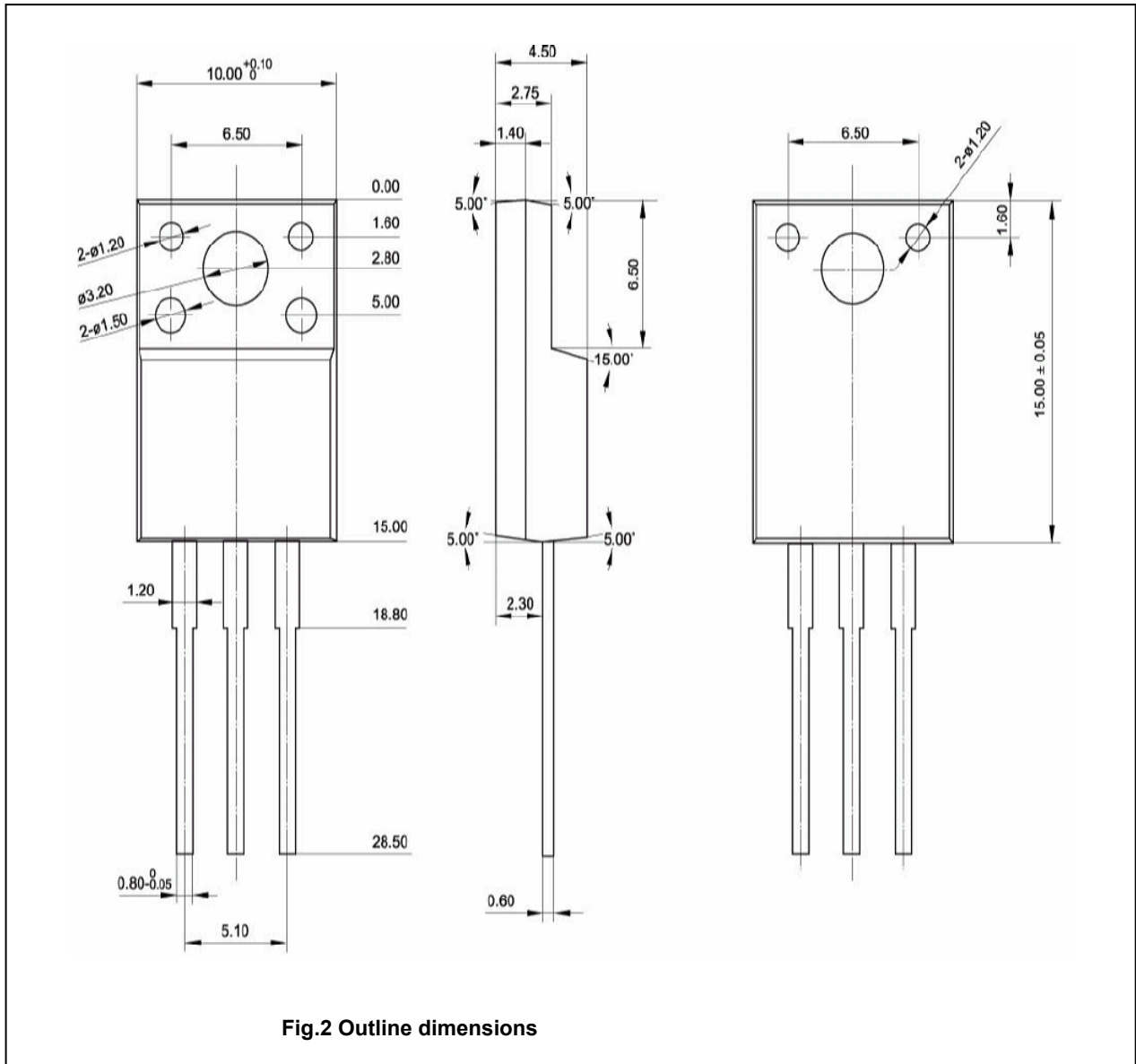


Fig.2 Outline dimensions

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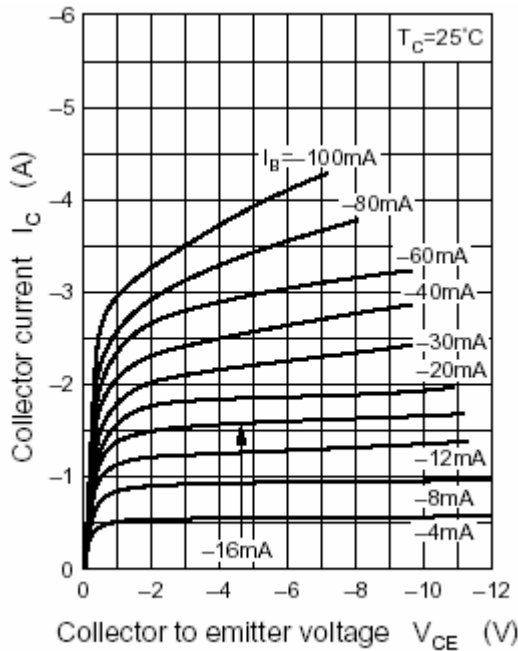


Fig.3 Static Characteristic

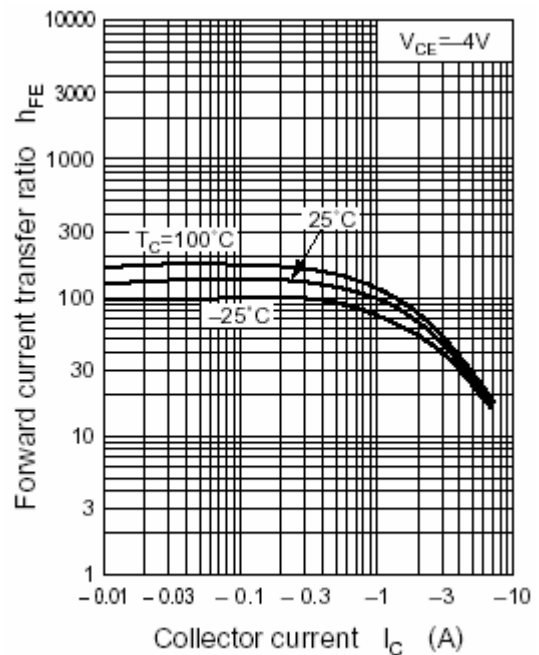


Fig.4 DC current Gain

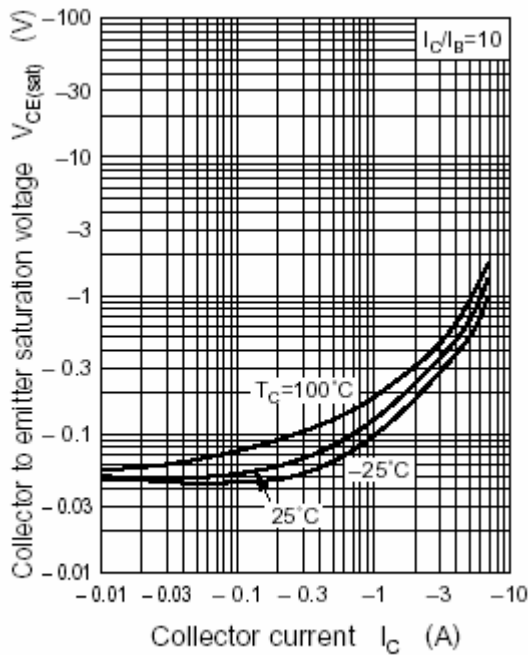


Fig.5 Collector-Emitter Saturation Voltage

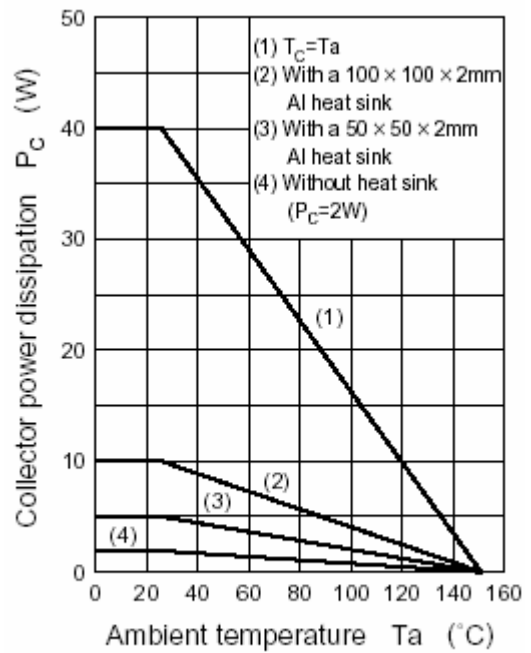


Fig.4 Power Derating